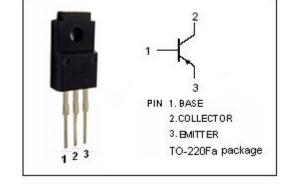


## **ISC Silicon PNP Power Transistor**

# 2SA1442

### **DESCRIPTION**

- Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= -60V(Min)
- · High DC Current Gain-
  - :  $h_{FE}$ = 100(Min)@ ( $V_{CE}$ = -2V ,  $I_{C}$ = -1.5A)
- · Low Saturation Voltage-
- :  $V_{CE(sat)} = -0.3V(Max)@ (I_C = -4A, I_B = -0.2A)$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

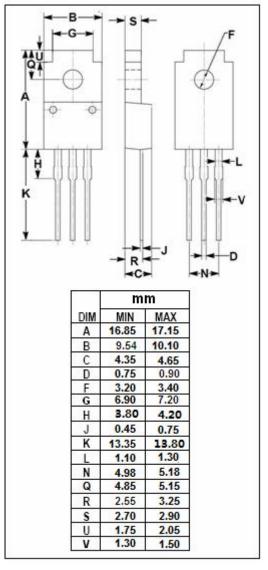


#### **APPLICATIONS**

 This type of power transistor is developed for high-speed switching and features a high h<sub>FE</sub> at low V<sub>CE(sat)</sub>, which is ideal for use as a driver in DC/DC converters and actuators.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-100	V	
Vceo	Collector-Emitter Voltage	-60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-7.0	٧	
Ic	Collector Current-Continuous	-7.0	Α	
Ісм	Collector Current-Pulse	-14	Α	
I <sub>B</sub>	Base Current-Continuous	-3.5	Α	
P <sub>T</sub>	Total Power Dissipation @T <sub>C</sub> =25℃	30	W	
	Total Power Dissipation @T <sub>a</sub> =25°C	2.0		
TJ	Junction Temperature	150		
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$	





# **ISC Silicon PNP Power Transistor**

2SA1442

## **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -4.0A; I <sub>B</sub> = -0.4A, L= 1mH	-60			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.2A			-0.3	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.3A			-0.5	V
V <sub>BE</sub> (sat)-1	Base-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.2A			-1.2	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.3A			-1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -60V ; I <sub>E</sub> =0			-10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.7A; V <sub>CE</sub> = -2V	100			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -1.5A ; V <sub>CE</sub> = -2V	100		400	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -4.0A ; V <sub>CE</sub> = -2V	60			

#### ♦ h<sub>FE-2</sub> Classifications

M	L	K
100-200	150-300	200-400

## **NOTICE:**

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